

# Design of a detection system to obtain 2D axial dose maps for complex radiotherapy treatment verification

Presented by Maria Cristina Battaglia ([mbattaglia@us.es](mailto:mbattaglia@us.es)) on behalf of RADIA collaboration:

M.C. Battaglia<sup>1</sup>, M. A. G. Alvarez <sup>1,2,3</sup>, J. M. Espino <sup>1,2</sup>, M. I. Gallardo <sup>2</sup>, M. Ovejero <sup>1,2</sup>, Z. Abou-Haidar <sup>1</sup>, M. A. Cortés-Giraldo <sup>2</sup>, R. Arráns <sup>4</sup>, A. Pérez Vega-Leal <sup>5</sup>, J. M. Quesada <sup>2</sup>, A. Selva <sup>2,6</sup>

<sup>1</sup> Centro Nacional de Aceleradores (CNA), 41092 Seville, Spain.

<sup>2</sup> Departamento de Física Atómica, Molecular y Nuclear (FAMN), Universidad de Sevilla, 41012 Seville, Spain.

<sup>3</sup> Instituto de Física da Universidade de São Paulo (IFUSP), 05508-090, São Paulo, Brazil.

<sup>4</sup> Hospital Universitario Virgen Macarena, 41009 Seville, Spain.

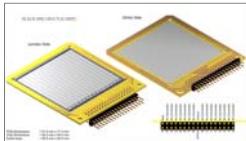
<sup>5</sup> Departamento de Ingeniería Electrónica, Universidad de Sevilla, 41092 Seville, Spain

<sup>6</sup> Dipartimento di Fisica e Astronomia 'Galileo Galilei', Università degli studi di Padova, Italy



## TWO DETECTORS

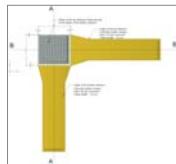
A feasibility study <sup>(1),(2),(3)</sup>:  
First detector (W1-SS 500)



Single Sided Silicon Strip Detector (SSSSD)

## New detector (BB7 technology)

Designed considering clinical constraints.  
Developed by RADIA collaboration and the companies:  
Micron Semiconductors Ltd. & ATI Sistemas S. L.



Dual chip SSSSD



ATI SISTEMAS

MICRON SEMICONDUCTOR Ltd

## DETECTORS CHARACTERISTICS

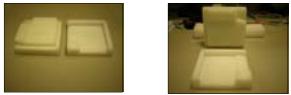
Characteristics	W1(SS)-500 detector	Dual chip SSSSD BB7
Nº Wafers	1	2
Nº Junction elements on Wafer 1	16	32
Nº Junction elements on Wafer 2	N/A	32 (perpendicular to strips on wafer 1)
Element length	49.5 mm	64 mm
Element pitch	3.1 mm	2.1 mm
Element width	3000.0 $\mu$ m	2000.0 $\mu$ m
Active Area	50x50mm <sup>2</sup>	64x64mm <sup>2</sup>
Wafer Thickness	500 $\mu$ m	500 $\mu$ m
Element active volume	49.5x3.0x0.5mm <sup>3</sup>	64.0x2.0x0.5 mm <sup>3</sup>
Metalization	Aluminum 0.3 $\mu$ m	Aluminum 0.3 $\mu$ m
Package	PCB with edge connections	Kapton with 20cm cables
Structure material	FR4 (1.85g/cm <sup>3</sup> )	Kapton (1.6 g/cm <sup>3</sup> )

## FIRST TESTS: CHARACTERIZATION OF THE DETECTOR IN STANDARD REFERENCE CONDITIONS:

### Material and Method:

#### Mechanical system

Box



#### Slab phantom



Inside

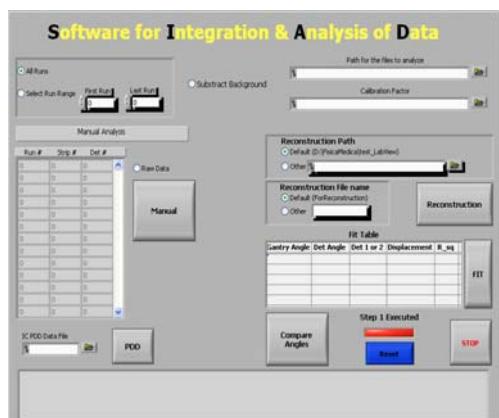
#### Experimental setup



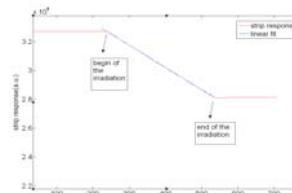
- ✓ Siemens PRIMUS Linear Accelerator (linac) (6 MV photon beam irradiation);
- ✓ Slab phantom;
- ✓ Detector + polyethylene box (orthogonal irradiation);
- ✓ Associated electronics (in-house developed);
- ✓ Labview platform for data acquisition.

## Preliminary data and analysis:

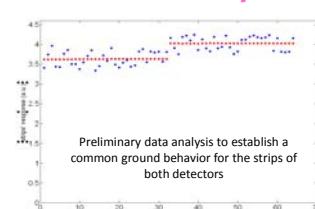
### Designed software interface



#### Strip's response



#### Uniformity



#### Linear response to the irradiation

Under calibration conditions:

- Source to Surface Distance=100cm
- 1.5cm of solid water

1MU of irradiation corresponds to 1cGy

First qualitative calibration in dose

## BIBLIOGRAPHY:

- (1) A. Bocci, M. A. Cortes-Giraldo, M. I. Gallardo, J. M. Espino, R. Arrans, M. A. G. Alvarez, Z. Abou-Haidar, J. M. Quesada, A. Perez Vega-Leal, and F. J. Perez Nieto, "Silicon strip detector for a novel 2D dosimetric method for a radiotherapy treatment verification", *Nucl. Instrum. Methods Phys. Res., Sect. A* **673**, 98 (2012).
  - (2) Z. Abou-Haidar, A. Bocci, M. A. G. Alvarez, J.M. Espino, M.I. Gallardo, M.A. Cortés-Giraldo, M.C. Ovejero, J.M. Quesada, R. Arráns, M. Ruiz Prieto, A. Pérez Vega-Leal y F.J. Pérez Nieto."Output factor determination for dose measurements in axial and perpendicular planes using a silicon strip detector", *Phys. Rev. ST Accel. Beams* **15**, 042802 (2012).
  - (3) M.A.Cortés-Giraldo, M.I. Gallardo, R. Arráns, J.M. Quesada, A. Bocci, J.M. Espino, Z. Abou-Haidar and M. A. G. Alvarez, "Geant4 simulation to study the sensitivity of a Micron silicon strip detector irradiated by a Siemens PRIMUS linac", *Progress in Nuclear Science and Technology*, Vol. 2, pp. 191-196 (2011).
  - (4) Patent at the OEMP - Oficina Española de Patentes y Marcas – Ministry of Industry & Commerce: Number P201101009 (13/09/2011).
- Acknowledgment:** appreciated contributions to make this project a success received from the silicon detector manufacturer, Micron Semiconductor Ltd., web: [www.micronsemiconductor.co.uk](http://www.micronsemiconductor.co.uk)  
(Dr Susanne Walsh Design / Colin D.Wilburn Director) and ATI Sistemas S. L., [www.atisistemas.com](http://www.atisistemas.com) (Mrs. Marta Trueba).